Data Sheet

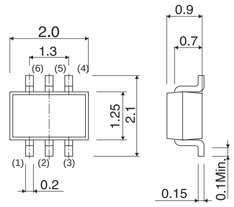
0.9V Drive Nch + Nch MOSFET

UM6K34N

● Structure
Silicon N-channel MOSFET

● Dimensions (Unit : mm)

UMT6
(SC-88)
<SOT-363>

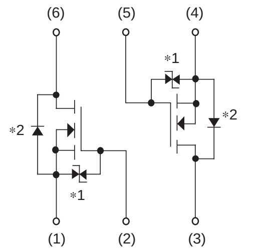


Abbreviated symbol : K34

● Features
1) Mounting cost and area can be cut in half.
2) Low On-resistance.
3) Low voltage drive(0.9Vdrive)makes this device ideal for portable equipment.

● Application
Interfacing, Switching

● Inner circuit



(1) Tr1 Source
(2) Tr1 Gate
(3) Tr2 Drain
(4) Tr2 Source
(5) Tr2 Gate
(6) Tr1 Drain

∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

● Packaging specifications

Type	Package	Taping
	Code	TCN
	Basic ordering unit (pieces)	3000
UM6K34N		O

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	50	V
Gate-source voltage		V_{GSS}	±8	V
Drain current	Continuous	I_D	±200	mA
	Pulsed	I_{DP} *1	±800	mA
Source current (Body Diode)	Continuous	I_s	125	mA
	Pulsed	I_{sp} *1	800	mA
Power dissipation		P_D *2	150	mW / TOTAL
			120	mW / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Each terminal mounted on a recommended land.

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	833	°C / W /TOTAL
		1042	°C / W /ELEMENT

* Each terminal mounted on a recommended land.

● **Electrical characteristics** (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±8V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=50V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS(on)}$ *	-	1.6	2.2	Ω	I_D=200mA, V_{GS}=4.5V
		-	1.7	2.4		I_D=200mA, V_{GS}=2.5V
		-	2.0	2.8		I_D=200mA, V_{GS}=1.5V
		-	2.2	3.3		I_D=100mA, V_{GS}=1.2V
		-	3.0	9.0		I_D=10mA, V_{GS}=0.9V
Forward transfer admittance	$\|Y_{fs}\|$ *	0.2	-	-	S	I_D=200mA, V_{DS}=10V
Input capacitance	C_{iss}	-	26	-	pF	V_{DS}=10V
Output capacitance	C_{oss}	-	6	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	3	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$ *	-	5	-	ns	I_D=100mA, V_{DD}≒25V
Rise time	t_r *	-	8	-	ns	V_{GS}=4.5V
Turn-off delay time	$t_{d(off)}$ *	-	17	-	ns	R_L=250Ω
Fall time	t_f *	-	43	-	ns	R_G=10Ω

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD} *	-	-	1.2	V	I_s=200mA, V_{GS}=0V

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics(Ⅰ)

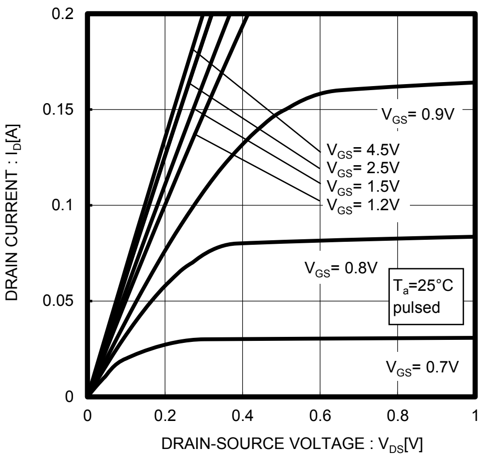


Fig.2 Typical Output Characteristics(Ⅱ)

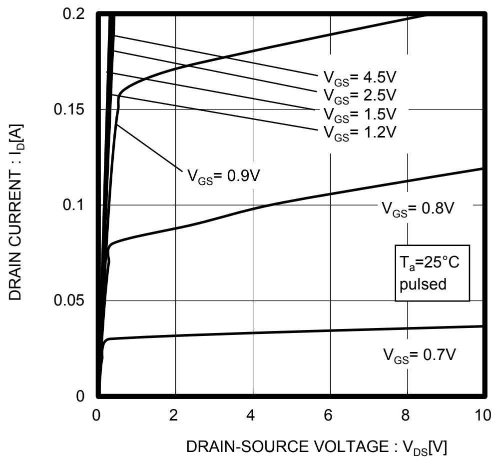


Fig.3 Typical Transfer Characteristics

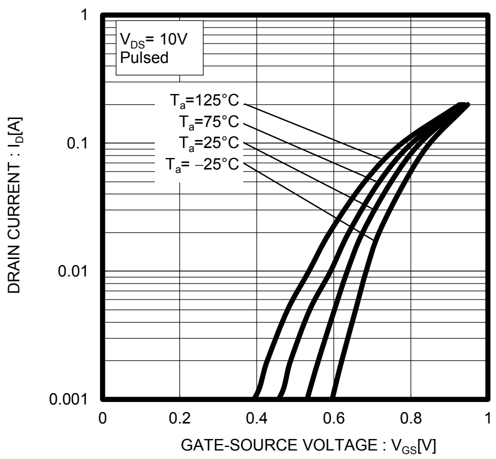


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(Ⅰ)

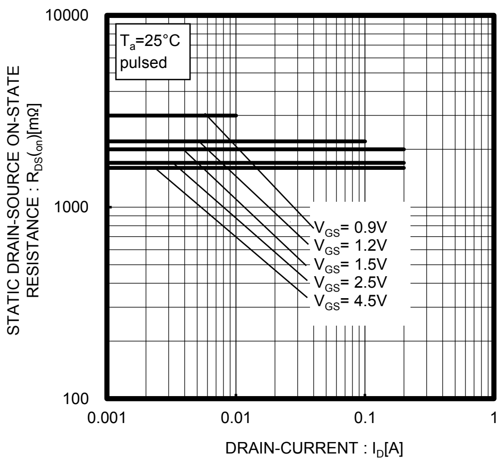


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(Ⅱ)

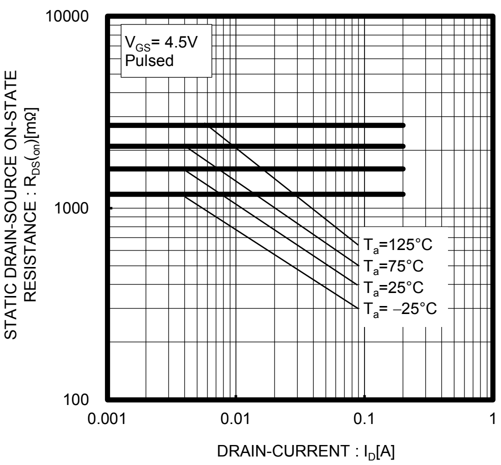


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

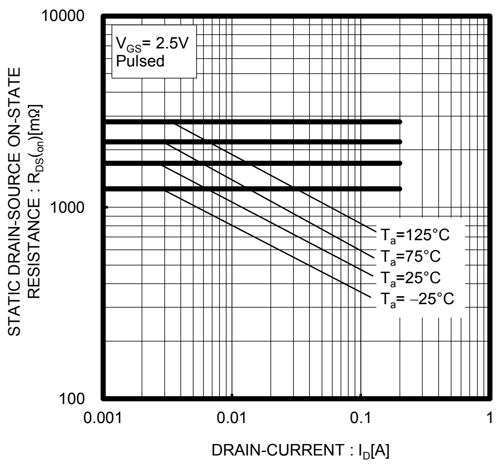


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(Ⅳ)

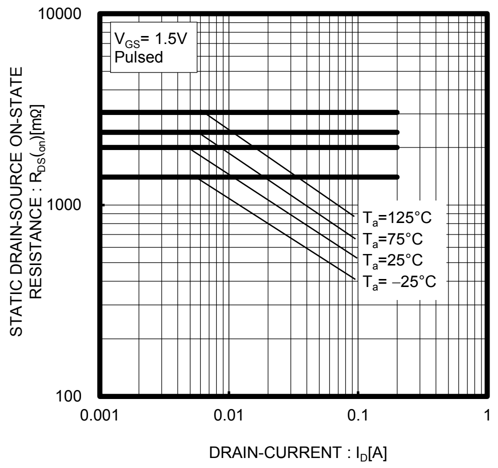


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(Ⅴ)

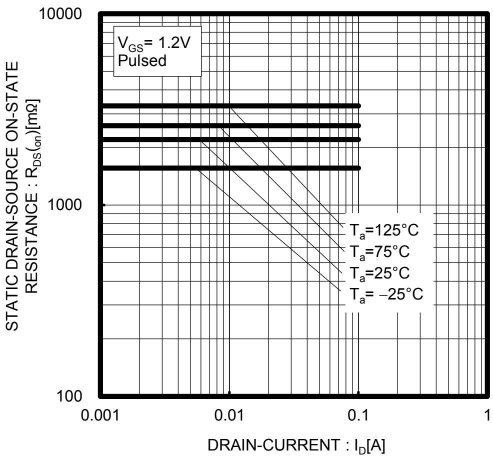


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current(Ⅵ)

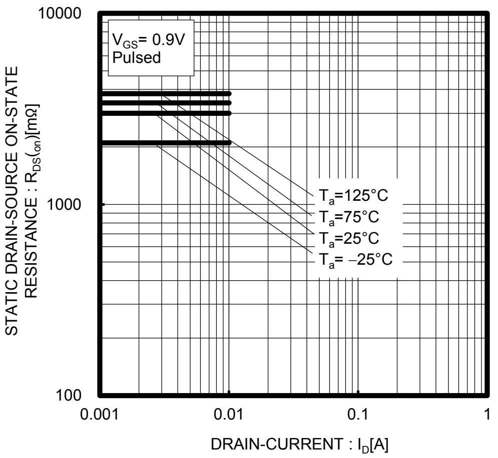


Fig.10 Forward Transfer Admittance vs. Drain Current

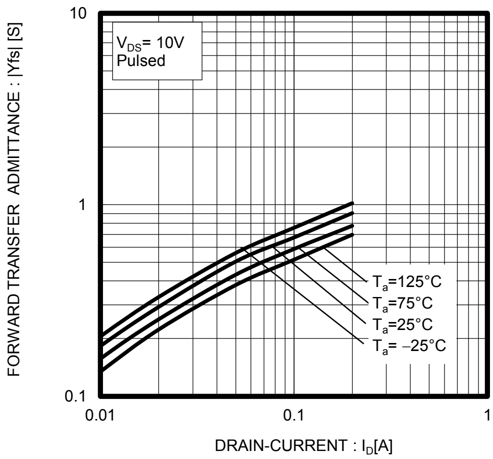


Fig.11 Reverse Drain Current vs. Sourse-Drain Voltage

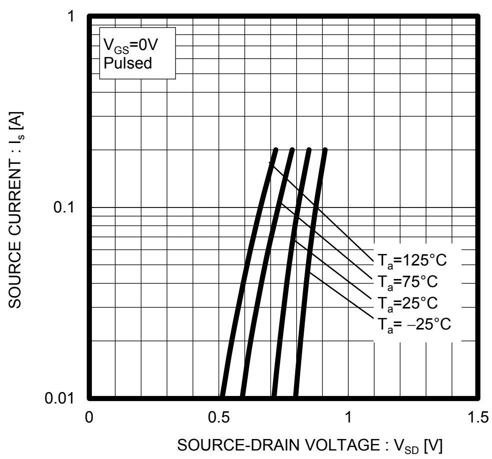


Fig.12 Static Drain-Source On-State Resistance vs. Gate Source Voltage

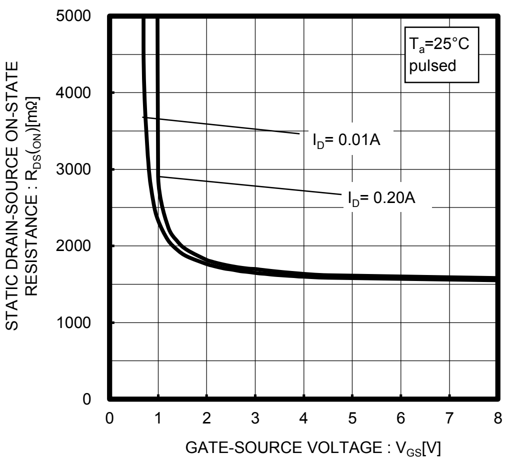


Fig.13 Switching Characteristics

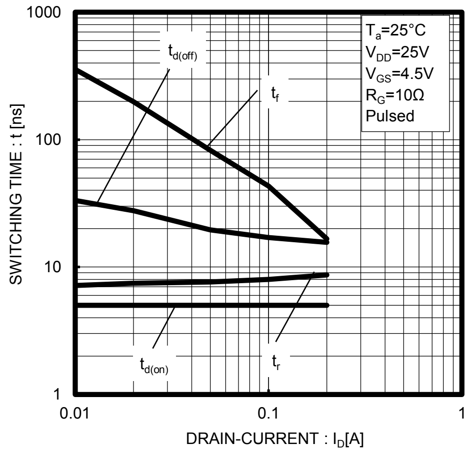


Fig.14 Typical Capacitance vs. Drain-Source Voltage

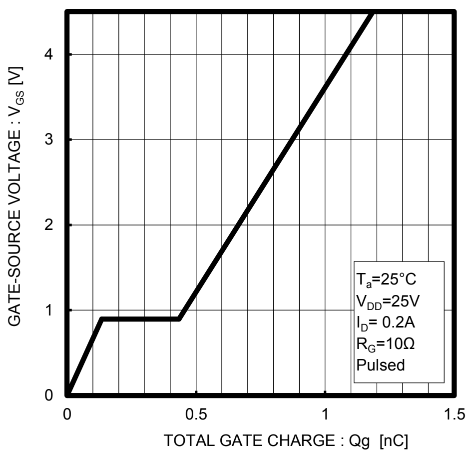
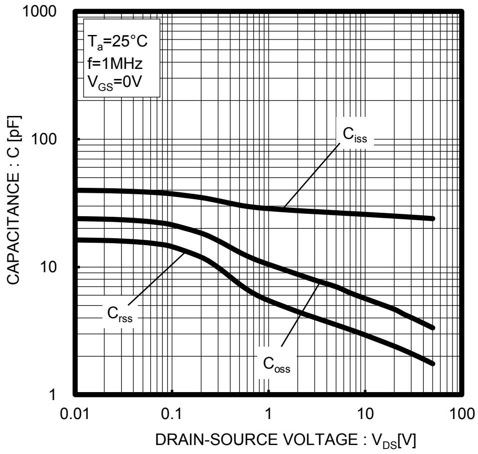


Fig.15 Typical Capacitance vs. Drain-Source Voltage



● **Measurement circuits**

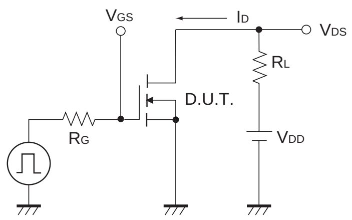


Fig.1-1 Switching Time Measurement Circuit

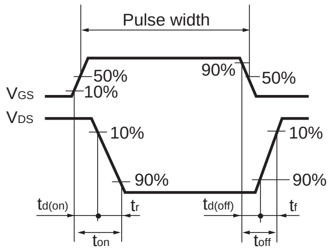


Fig.1-2 Switching Waveforms

● **Notice**

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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